

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method, comprising:
~~exciting an undesirable bond in an atomic layer deposition (ALD) formed film to an energy level sufficient to activate the undesirable bond and insufficient to activate a desirable bond~~
forming a film with an atomic layer deposition (ALD) containing metal-metal bonds and metal-oxide bonds, subsequently applying energy to said film sufficient to disassociate the metal-metal bonds, but insufficient to disassociate the metal-oxide bonds..
2. (Original) The method of claim 1, further comprising:
after exciting the undesirable bond, exposing the film to a reactant.
3. (Original) The method of claim 2, wherein the reactant is an oxygen source.
4. (Original) The method of claim 3, wherein the oxygen source is water.
5. (Original) The method of claim 2, wherein the reactant comprises a metal precursor.
6. (Original) The method of claim 5, wherein the metal is one of zirconium, titanium, aluminum, gallium, cesium, indium, hafnium, tantalum, praseodymium, niobium, scandium, lutetium, cerium and lanthanum.
7. (Cancelled)
8. (Original) The method of claim 7, wherein the metal is selected from a group consisting of zirconium, titanium, aluminum, gallium, cesium, indium, hafnium, tantalum, praseodymium, niobium, scandium, lutetium, cerium and lanthanum.
9. (Original) The method of claim 1, wherein the film is a metal oxide film.

10. (Original) The method of claim 1, wherein exciting the undesirable bonds comprises exposing the undesirable bonds to electromagnetic radiation.

11-20 (Canceled)

21. (Currently Amended) A method, comprising:

~~modifying undesirable bonds in an atomic layer deposition (ALD) formed film by exciting the undesirable bond to an energy level sufficient to activate the undesirable bonds and insufficient to activate desirable bonds~~forming a film with an atomic layer deposition (ALD) containing metal-metal bonds and metal-oxide bonds, subsequently applying energy to said film sufficient to disassociate the metal-metal bonds, but insufficient to disassociate the metal-oxide bonds; and
exposing the film to a reactant.

22. (Original) The method of claim 21, wherein modifying the undesirable bonds comprises reducing the number of undesirable bonds on the film.

23. (Original) The method of claim 21, wherein modifying the undesirable bonds comprises minimizing the number of undesirable bonds on the film.